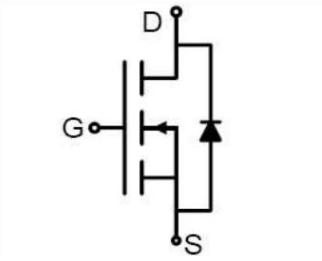
AP30H220G

N-Channel Enhancement Mosfet

DATA SHEET

Feature

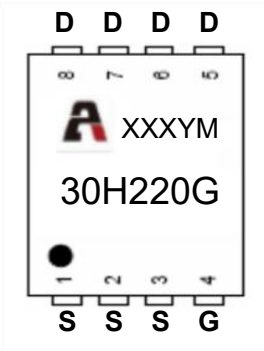
- 30V,150A
  $R_{DS(ON)}$ <1.8mΩ @V_{GS}=10V TYP: 1.4mΩ
  $R_{DS(ON)}$ <3.2mΩ @V_{GS}=4.5V TYP: 2.3mΩ
- Advanced Trench Technology
- Lead free product is acquired
- Excellent $R_{DS(ON)}$ and Low Gate Charge



Schematic Diagram

Application

- PWM applications
- Load Switch
- Power management



Marking and pin Assignment

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity (PCS)
30H220G	AP30H220G	PDFN5X6	-	-	5000

ABSOLUTE MAXIMUM RATINGS (T_J=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current (Tc=25℃) (1)	I_D	150	A
Continuous Drain Current (Tc=100℃)	I_D	84	A
Pulsed Drain Current (1)	I_{DM}	600	A
Single Pulsed Avalanche Energy (2)	E_{AS}	441	mJ
Power Dissipation	P_D	128	W
Thermal Resistance from Junction to Case	$R_{\theta JC}$	0.97	℃/W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{STG}	-55~ +150	℃

Notes:

1) Repetitive Rating: pulse width limited by maximum junction temperature
2) EAS condition : T_J=25℃, V_{DD}=20V, V_G=10V, L=0.5mH, R_g=25Ω, I_{AS}=42A

MOSFET ELECTRICAL CHARACTERISTICS(T_J=25℃ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D =250μA	30	-	-	V
Zero gate voltage drain current	I_{DSS}	V_{DS} = 30V, V_{GS} = 0V	-	-	1	μA
Gate-body leakage current	I_{GSS}	V_{GS} =±20V, V_{DS} = 0V	-	-	±100	nA
Gate threshold voltage	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =250μA	1	1.6	2.5	V
Drain-source on-resistance	$R_{DS(on)}$	V_{GS} =10V, I_D =30A	-	1.4	1.8	mΩ
		V_{GS} =4.5V, I_D =20A	-	2.3	3.2	
Dynamic characteristics						
Input Capacitance	C_{iss}	V_{DS} =15V, V_{GS} =0V, f =1MHz	-	6847	-	pF
Output Capacitance	C_{oss}		-	940	-	
Reverse Transfer Capacitance	C_{rss}		-	604	-	
Switching characteristics						
Turn-on delay time	$t_{d(on)}$	V_{DD}=15V, I_D=30A, R_L=1Ω V_{GS}=10V, R_G=3Ω	-	16	-	ns
Turn-on rise time	t_r		-	9	-	
Turn-off delay time	$t_{d(off)}$		-	65	-	
Turn-off fall time	t_f		-	18	-	
Total Gate Charge	Qg	VDS=15V, ID=30A, VGS=10V	-	93	-	nC
Gate-Source Charge	Qgs		-	14	-	
Gate-Drain Charge	Qgd		-	21	-	
Source-Drain Diode characteristics						
Diode Forward voltage	V_{DS}	V_{GS} =0V, I_S=30A	-	-	1.2	V
Diode Forward current	I_S		-	-	150	A

Test Circuit

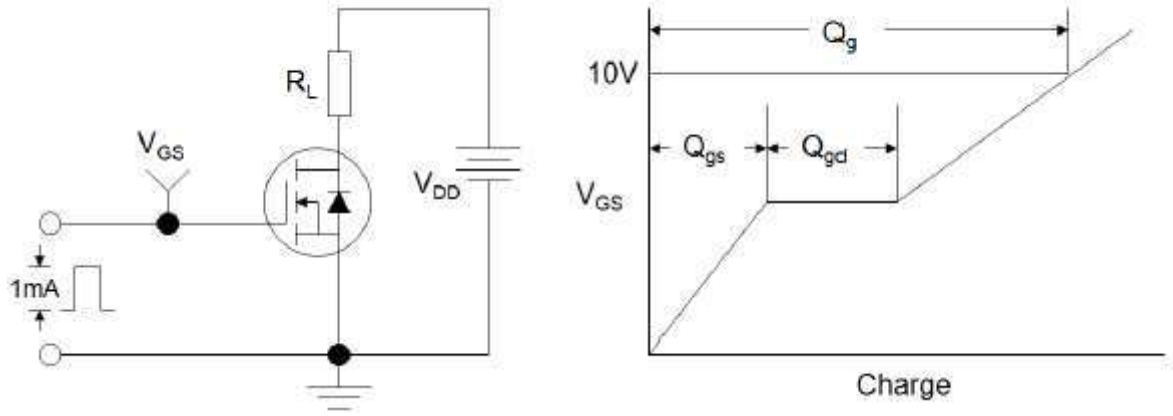


Figure1:Gate Charge Test Circuit & Waveform

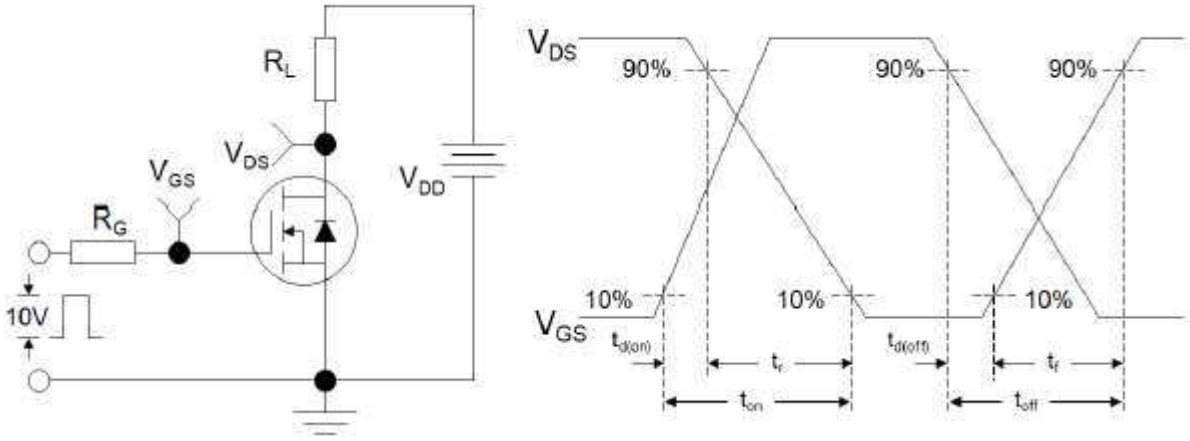


Figure 2: Resistive Switching Test Circuit & Waveforms

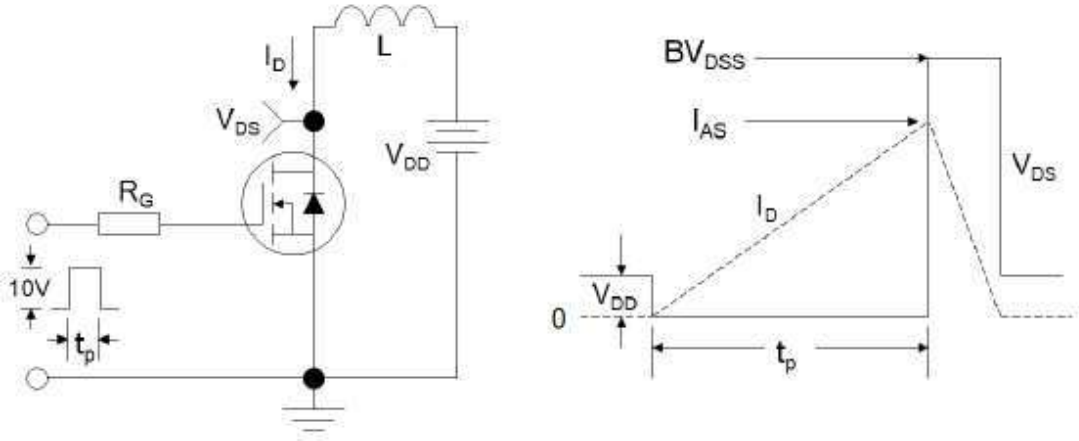


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms

Typical Performance Characteristics

Figure1: Output Characteristics

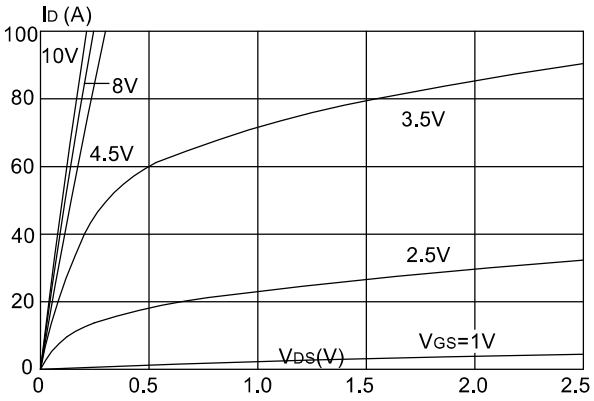


Figure 2: Typical Transfer Characteristics

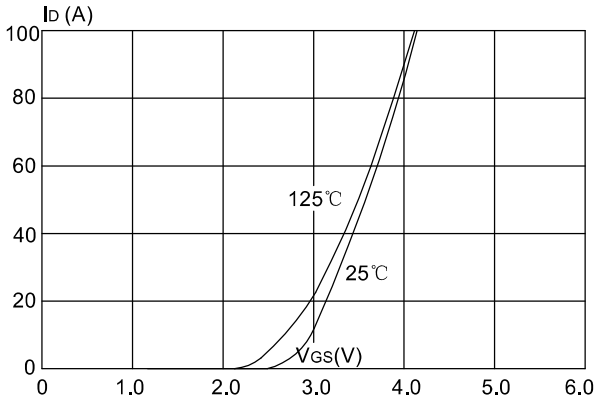


Figure 3: On-resistance vs. Drain Current

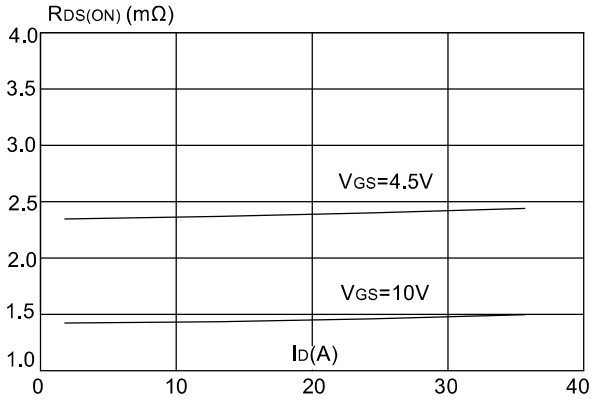


Figure 4: Body Diode Characteristics

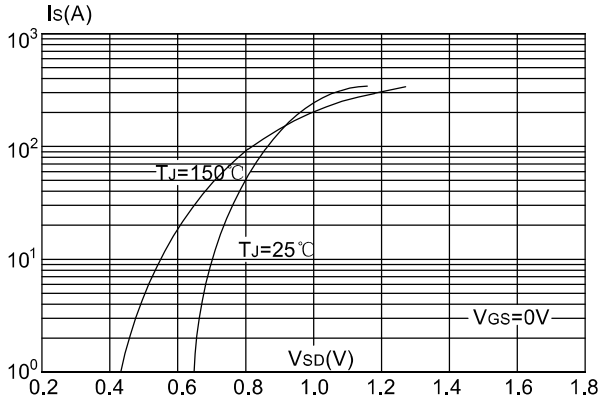


Figure 5: Gate Charge Characteristics

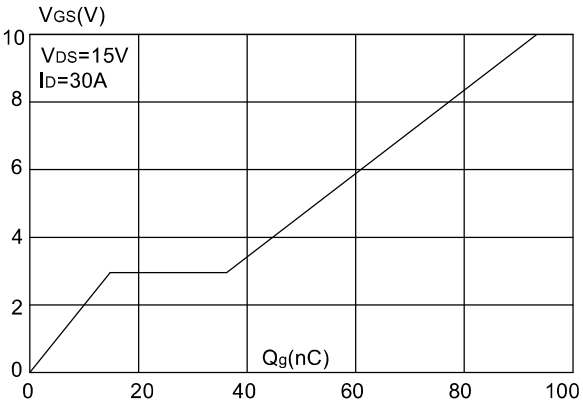
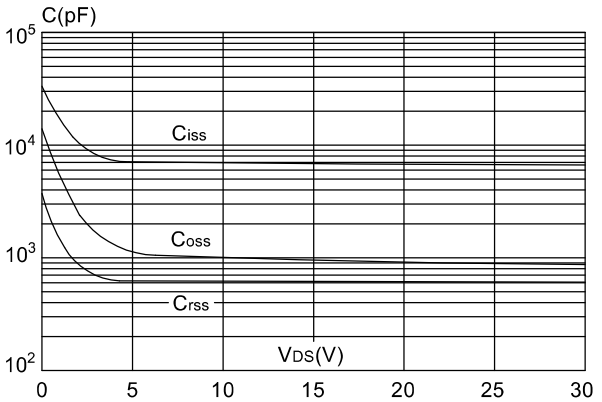


Figure 6: Capacitance Characteristics



Typical Performance Characteristics

Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

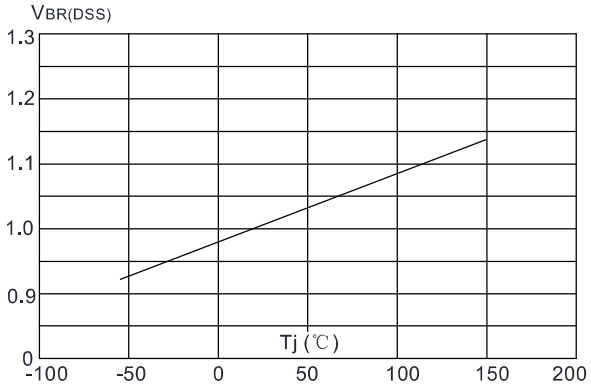


Figure 8: Normalized on Resistance vs. Junction Temperature

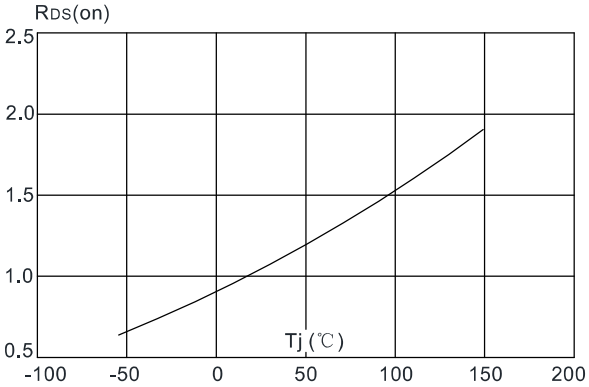


Figure 9: Maximum Safe Operating Area

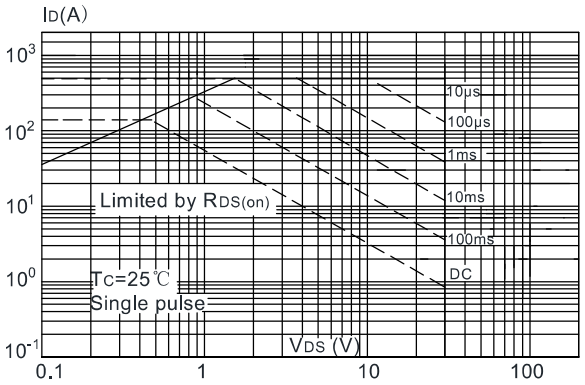


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

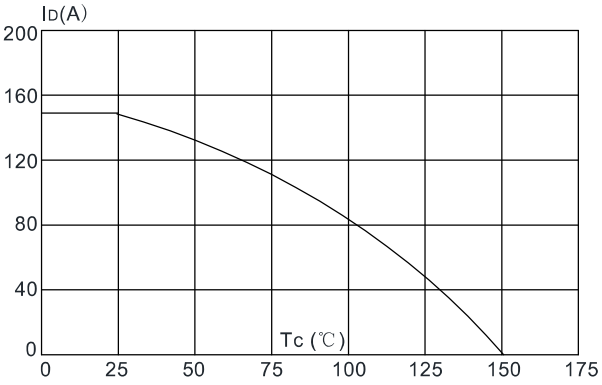
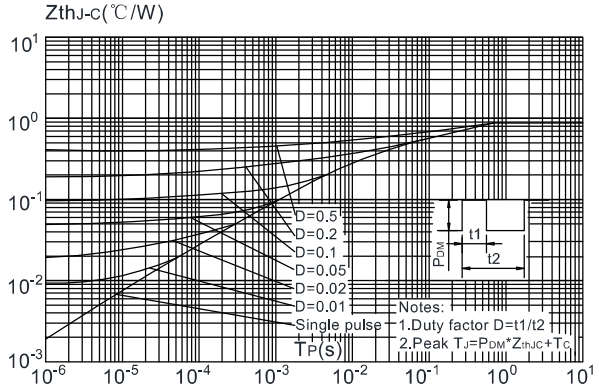
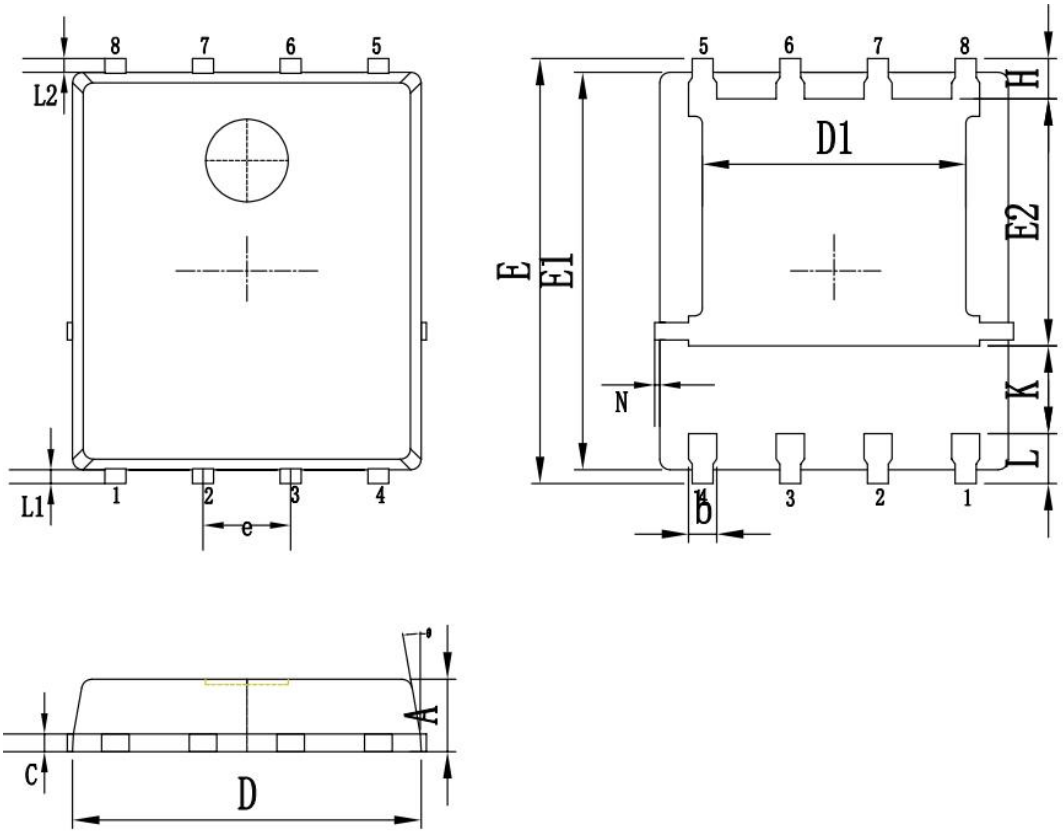


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



PDFN5X6 Package Information



Symbols	Millimeters		
	MIN.	NOM.	MAX.
A	0.90	1.05	1.20
b	0.20	0.40	0.50
C	0.20	0.25	0.35
D	4.80	5.05	5.20
D1	3.80	3.90	4.10
E	5.90	6.00	6.20
E1	5.60	5.75	5.90
E2	3.40	3.50	3.60
e	1.27 BSC.		
H	0.40	0.60	0.70
K	1.17	1.27	1.37
L	0.50	0.74	0.84
L1/L2	0.10	0.16	0.20
θ	8°	10°	12°
N	0	-	0.15

Revision History

Revision	Release	Remark
V1.0	2023/04/15	Initial Release

Disclaimer

The information given in this document describes the independent performance of the product,but similar performance is not guaranteed under other working conditions,and cannot be guaranteed when installed with other products or equipment.To achieve the required performance of the product in actual scenarios,the customer should conduct a complete application test to assess the functionality of the product.

Allpower assumes no responsibility for equipment failures result from using products at values that exceed the ratings,operating conditions,or other parameters listed in the product specifications.

The product described in this specification is not applicable for aerospace or other applications which
requires high reliability.Customers using or selling these products for use in medical,life-saving,or life-sustaining applications do so at their own risk and agree to fully indemnify.

Due to product or technical improvements,the information described or contained herein may be changed without prior notice.